



High Quality Audio Dual Operational Amplifier

■ GENERAL DESCRIPTION

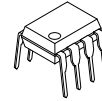
The **MUSES8820** is a high quality audio operational amplifier, which is optimized for high-end audio and professional audio applications.

It is the best for audio preamplifiers, active filters, and line amplifiers with excellent sound.

■ FEATURES

- Operating Voltage $V_{opr} = \pm 3.5V$ to $\pm 16V$
- Output noise $4.5nV/\sqrt{Hz}$ at $f=1kHz$
- Input Offset Voltage $0.3mV$ typ. $3mV$ max.
- Input Bias Current $100nA$ typ. $500nA$ max. at $T_a=25^\circ C$
- Voltage Gain $110dB$ typ.
- Slew Rate $5V/\mu s$ typ.
- Bipolar Technology
- Package Outline DIP8, SOP8 JEDEC 150mil

■ PACKAGE OUTLINE

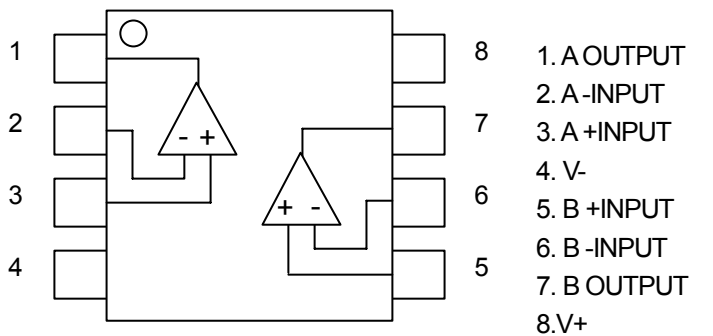


MUSES8820D
(DIP8)



MUSES8820E
(SOP8)

■ PIN CONFIGURATION



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MUSES8820

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Supply Voltage	V^+ / V^-	±18	V
Common Mode Input Voltage	V_{ICM}	±15 (Note1)	V
Differential Input Voltage	V_{ID}	±30	V
Power Dissipation	P_D	DIP8 : 870 SOP8 : 900(Note2)	mW
Output Current	I_O	±50	mA
Operating Temperature Range	T_{opr}	-40 to +85	°C
Storage Temperature Range	T_{stg}	-50 to +150	°C

(Note1) For supply Voltages less than ±15 V, the maximum input voltage is equal to the Supply Voltage.

(Note2) Mounted on the EIA/JEDEC standard board (114.3×76.2×1.6mm, two layer, FR-4).

■ RECOMMENDED OPERATING CONDITION (Ta=25°C)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Supply Voltage	V^+ / V^-	-	±3.5	-	±16	V

■ ELECTRIC CHARACTERISTICS

DC CHARACTERISTICS ($V^+ / V^- = \pm 15V$, Ta=25°C unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Operating Current	I_{cc}	No Signal, $R_L = \infty$	-	8.0	12.0	mA
Input Offset Voltage	V_{IO}	$R_s \leq 10k\Omega$ (Note3, 4)	-	0.3	3.0	mV
Input Bias Current	I_B	(Note3, 4)	-	100	500	nA
Input Offset Current	I_{IO}	(Note3, 4)	-	5	200	nA
Voltage Gain	A_V	$R_L \geq 2k\Omega$, $V_o = \pm 10V$ $R_s \leq 10k\Omega$	90	110	-	dB
Common Mode Rejection Ratio	CMR	$V_{ICM} = \pm 12V$ (Note5) $R_s \leq 10k\Omega$	80	110	-	dB
Supply Voltage Rejection Ratio	SVR	$V^+ / V^- = \pm 3.5$ to $\pm 16.0V$ $R_s \leq 10k\Omega$ (Note3, 6)	80	110	-	dB
Max Output Voltage	V_{OM}	$R_L = 2k\Omega$	±12	±13.5	-	V
Input Common Mode Voltage Range	V_{ICM}	CMR ≥ 80dB	±12	±13.5	-	V

(Note3) Measured at $V_{ICM} = 0V$

(Note4) Written by the absolute rate.

(Note5) CMR is calculated by specified change in offset voltage. ($V_{ICM} = 0V$ to +12V and $V_{ICM} = 0V$ to -12V)

(Note6) SVR is calculated by specified change in offset voltage. ($V^+ / V^- = \pm 3.5V$ to $\pm 16V$)

AC CHARACTERISTICS ($V^+V^- = \pm 15V$, $T_a = 25^\circ C$ unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gain Bandwidth Product	GB	$f = 10kHz$	-	11	-	MHz
Unity Gain Frequency	f_T	$A_V = +100, R_S = 100\Omega,$ $R_L = 2k\Omega, C_L = 10pF$	-	5.8	-	MHz
Phase Margin	ϕ_M	$A_V = +100, R_S = 100\Omega,$ $R_L = 2k\Omega, C_L = 10pF$	-	48	-	deg
Input Noise Voltage1	V_{NI}	$f = 1kHz, A_V = +100,$ $R_S = 100\Omega, R_L = \infty$	-	4.5	-	nV/ \sqrt{Hz}
Input Noise Voltage2	V_{N2}	$f = 1kHz, A_V = +10$ $R_S = 2.2k\Omega,$ RIAA, 30kHz LPF	-	0.8	1.4	μV_{rms}
Total Harmonic Distortion	THD	$f = 1kHz, A_V = +10,$ $R_L = 2k\Omega, V_o = 5V_{rms}$	-	0.001	-	%
Channel Separation	CS	$f = 1kHz, A_V = -+100,$ $R_S = 1k\Omega, R_L = 2k\Omega$	-	140	-	dB
Positive Slew Rate	+SR	$A_V = 1, V_{IN} = 2V_{p-p},$ $R_L = 2k\Omega, C_L = 10pF$	-	5	-	V/ μs
Negative Slew Rate	-SR	$A_V = 1, V_{IN} = 2V_{p-p},$ $R_L = 2k\Omega, C_L = 10pF$	-	5	-	V/ μs

■ Application Notes

•Package Power, Power Dissipation and Output Power

IC is heated by own operation and possibly gets damage when the junction power exceeds the acceptable value called Power Dissipation P_D . The dependence of the MUSES8820 P_D on ambient temperature is shown in Fig 1. The plots are depended on following two points. The first is P_D on ambient temperature 25°C, which is the maximum power dissipation. The second is 0W, which means that the IC cannot radiate any more. Conforming the maximum junction temperature T_{jmax} to the storage temperature T_{stg} derives this point. Fig.1 is drawn by connecting those points and conforming the P_D lower than 25°C to it on 25°C. The P_D is shown following formula as a function of the ambient temperature between those points.

$$\text{Dissipation Power } P_D = \frac{T_{jmax} - T_a}{\theta_{ja}} \text{ [W]} \quad (T_a=25^\circ\text{C to } T_a=150^\circ\text{C})$$

Where, θ_{ja} is heat thermal resistance which depends on parameters such as package material, frame material and so on. Therefore, P_D is different in each package.

While, the actual measurement of dissipation power on MUSES8820 is obtained using following equation.

$$(\text{Actual Dissipation Power}) = (\text{Supply Voltage } V_{DD}) \times (\text{Supply Current } I_{DD}) - (\text{Output Power } P_o)$$

The MUSES8820 should be operated in lower than P_D of the actual dissipation power.

To sustain the steady state operation, take account of the Dissipation Power and thermal design.

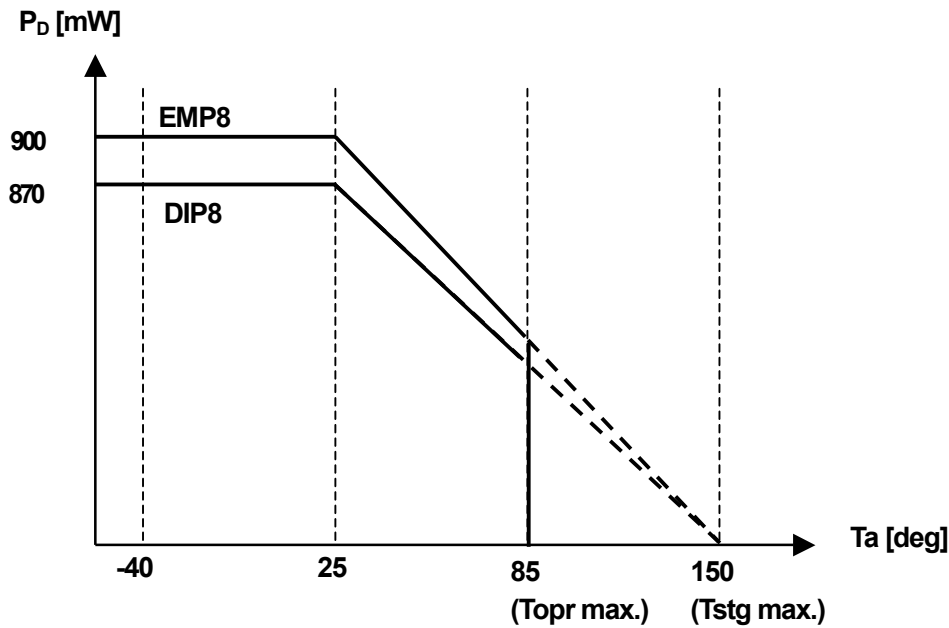
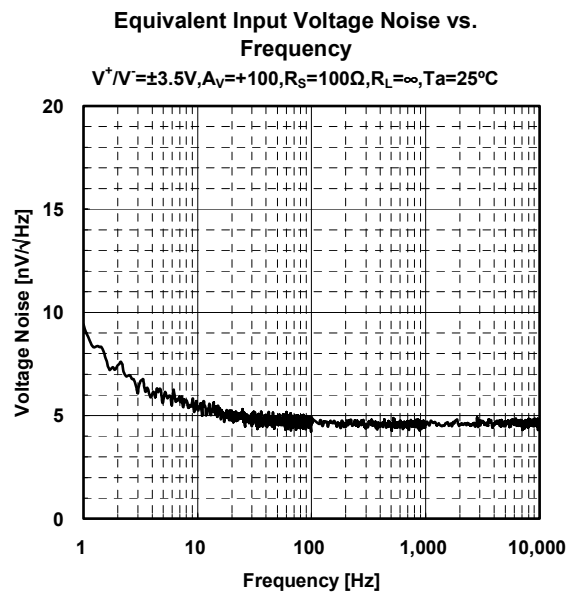
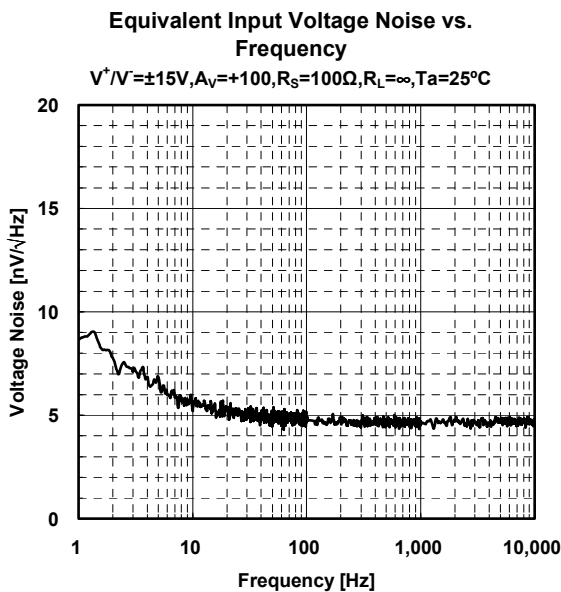
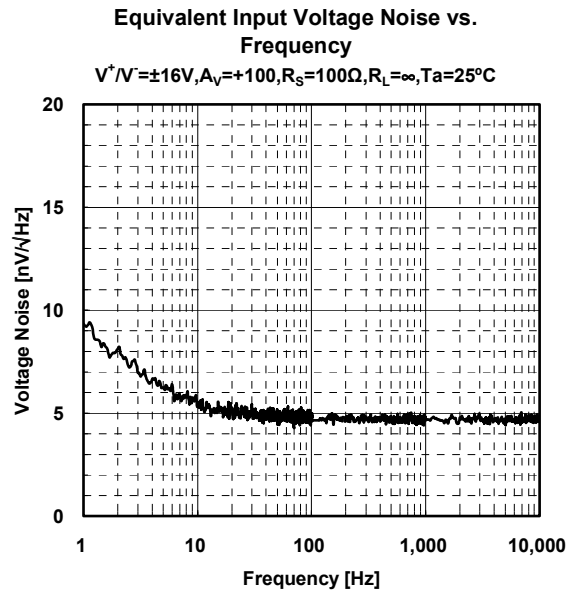
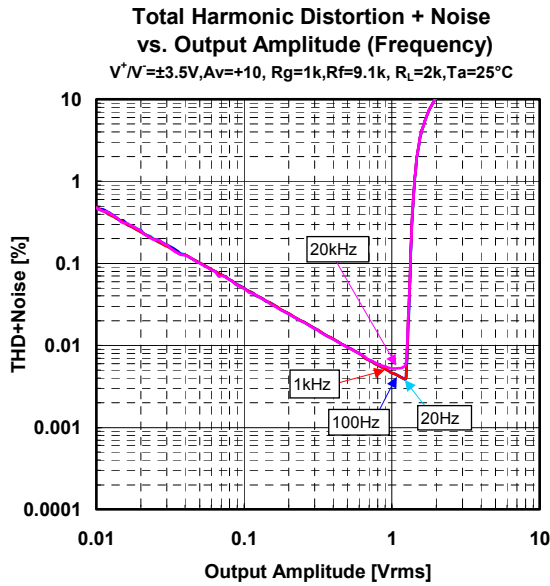
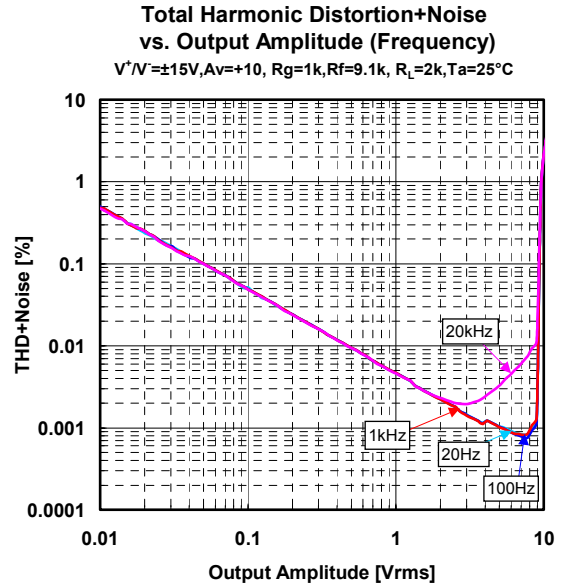
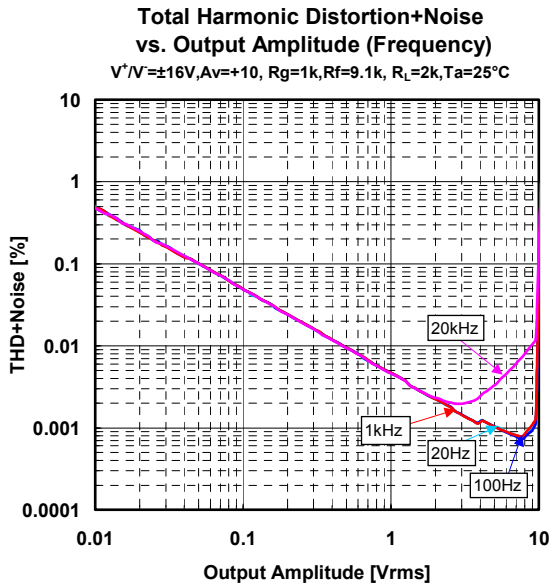
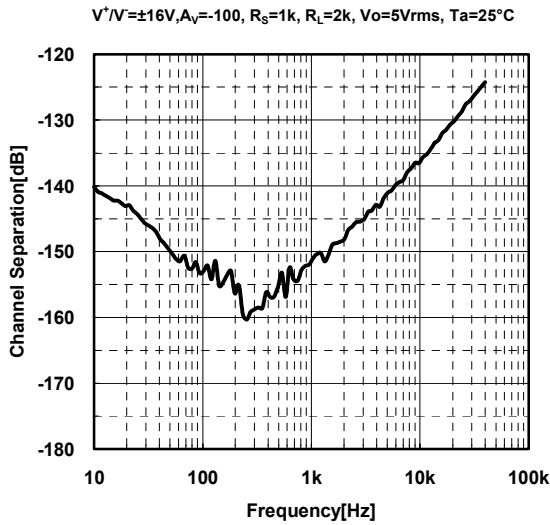


Fig.1 Power Dissipations vs. Ambient Temperature on the MUSES8820

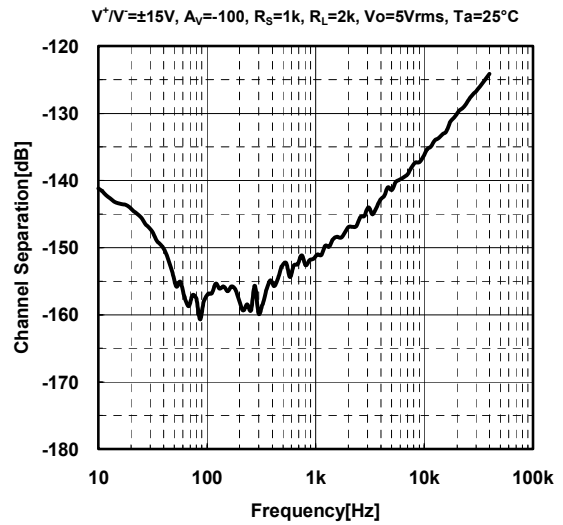
■ TYPICAL CHARACTERISTICS



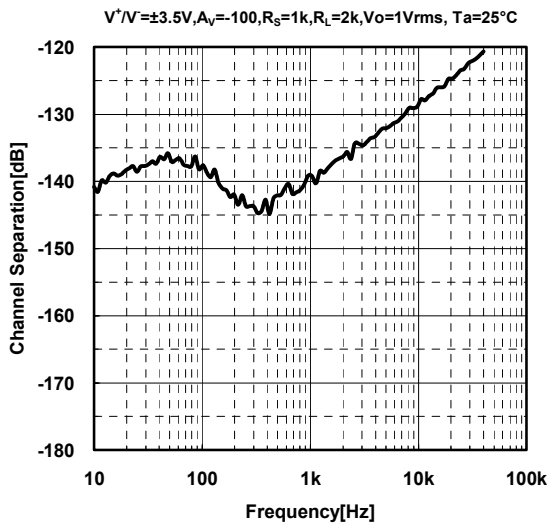
Channel Separation vs. Frequency



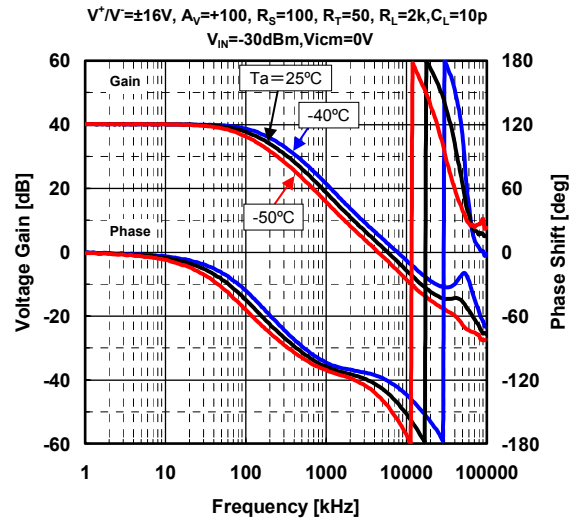
Channel Separation vs. Frequency



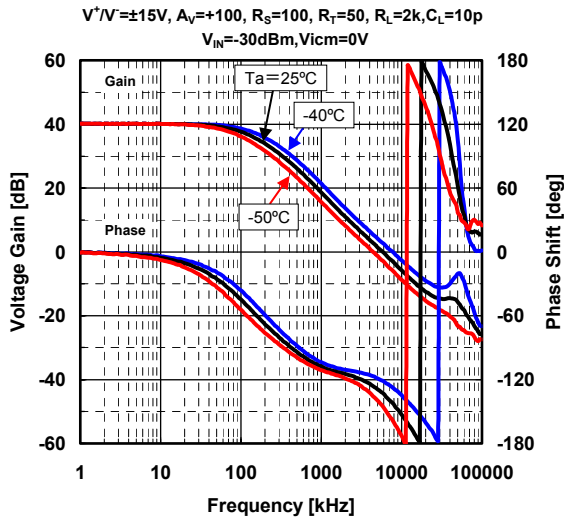
Channel Separation vs. Frequency



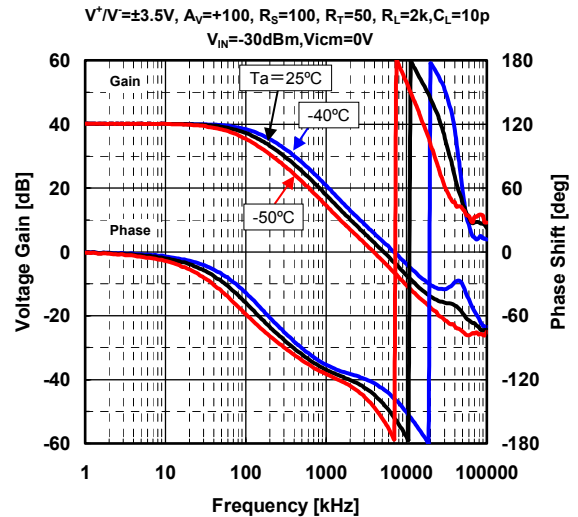
Closed-Loop Gain/Phase vs. Frequency(Temperature)



Closed-Loop Gain/Phase vs. Frequency(Temperature)

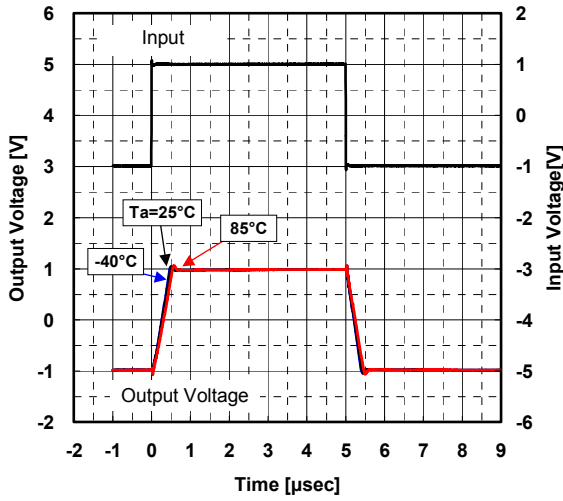


Closed-Loop Gain/Phase vs. Frequency(Temperature)



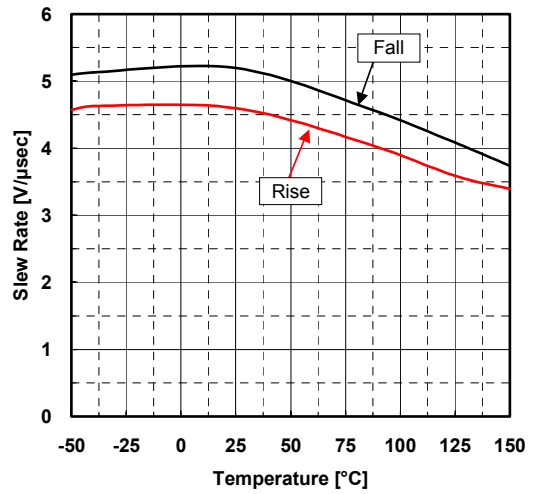
Transient Response (Temperature)

$V^+ / V^- = \pm 16V, V_{IN} = 2V_{P-P}, f = 100kHz$
 PulseEdge=10nsec, Gv=0dB, $C_L = 10p, R_L = 2k$



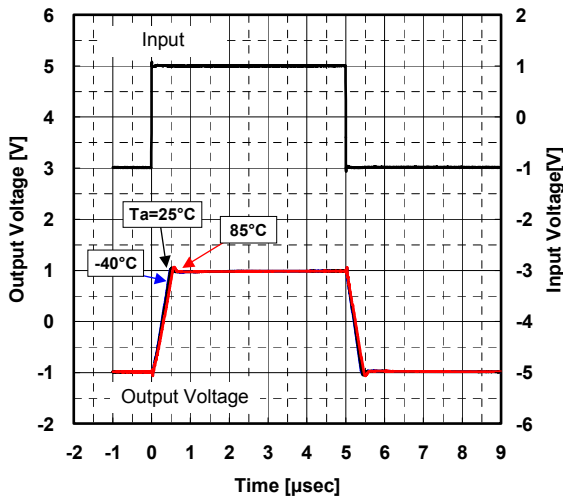
Slew Rate vs. Temperature

$V^+ / V^- = \pm 16V, V_{IN} = 2V_{P-P}, f = 100kHz$
 PulseEdge=10nsec, Gv=0dB, $C_L = 10p, R_L = 2k$



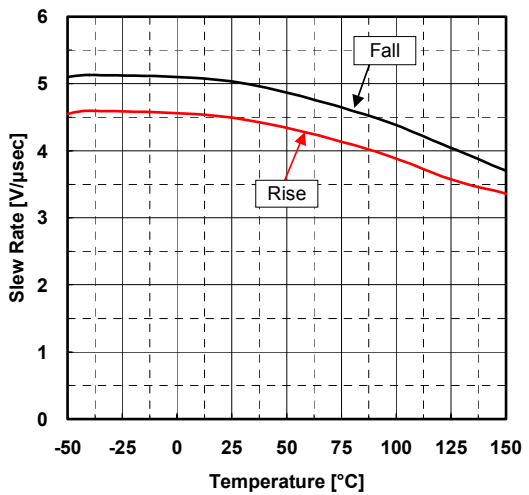
Transient Response (Temperature)

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 PulseEdge=10nsec, Gv=0dB, $C_L = 10p, R_L = 2k$



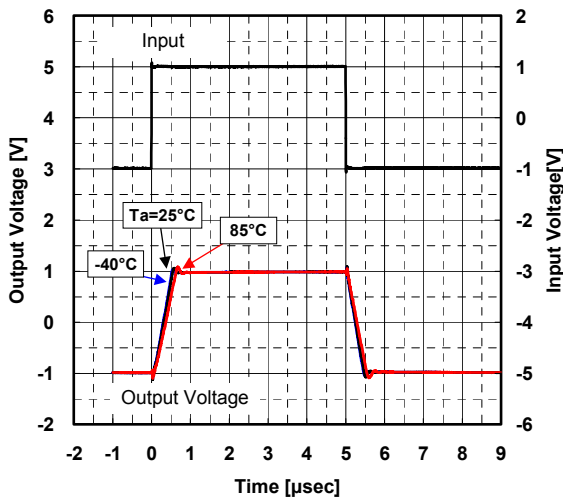
Slew Rate vs. Temperature

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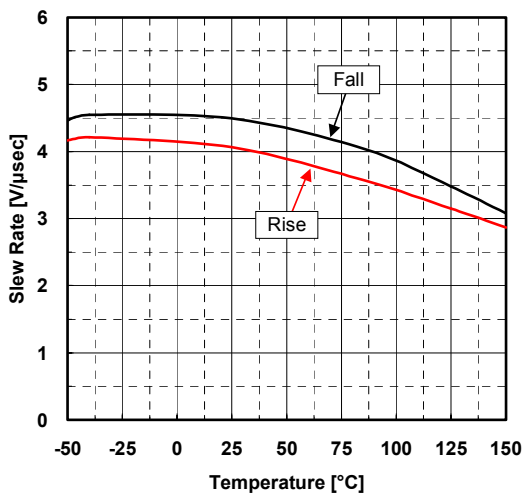
Transient Response (Temperature)

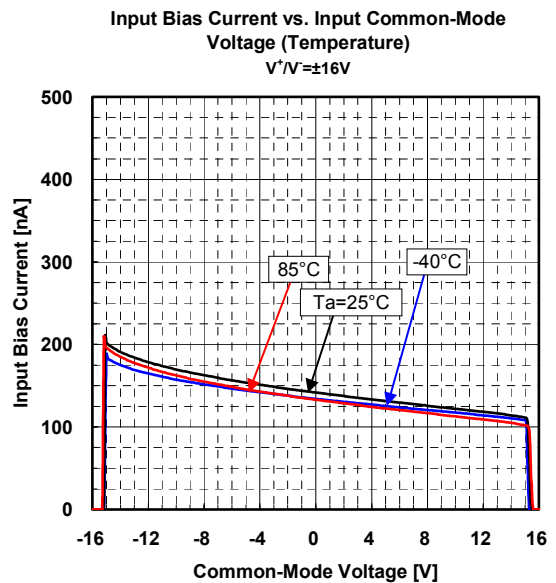
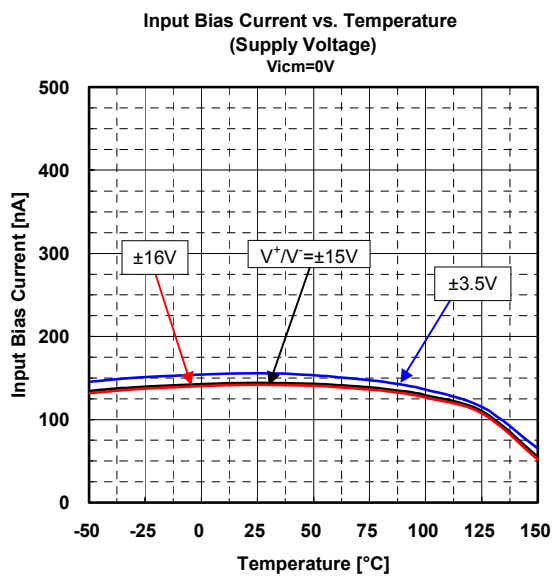
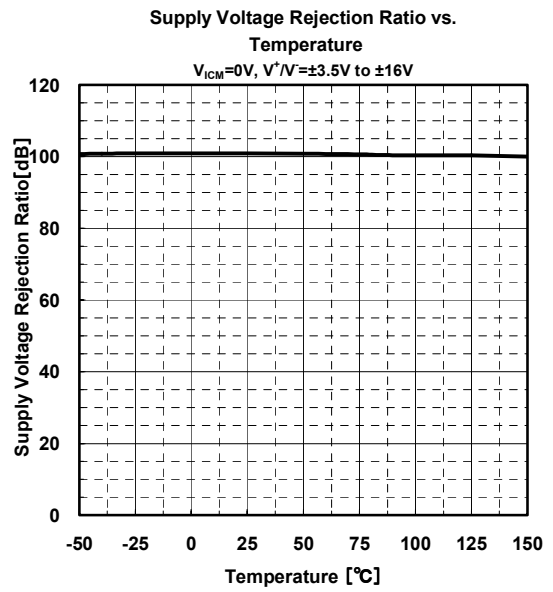
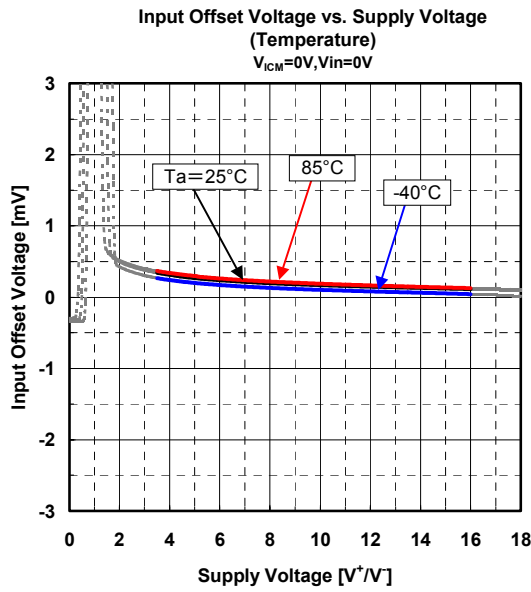
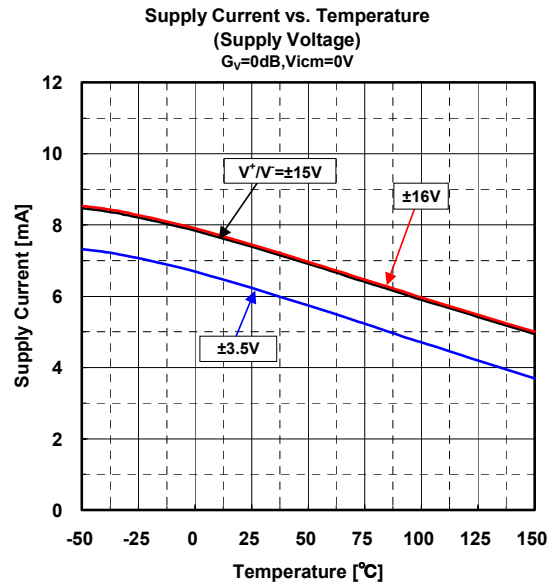
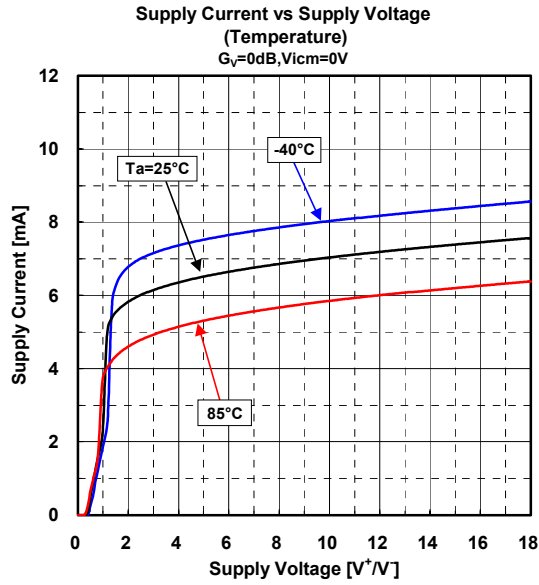
$V^+ / V^- = \pm 3.5V, V_{IN} = 2V_{P-P}, f = 100kHz$
 PulseEdge=10nsec, Gv=0dB, $C_L = 10p, R_L = 2k$



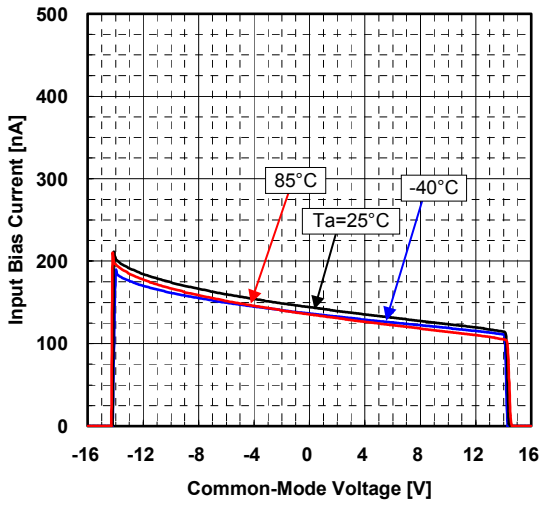
Slew Rate vs. Temperature

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 PulseEdge=10nsec, Gv=0dB, $C_L = 10p, R_L = 2k$

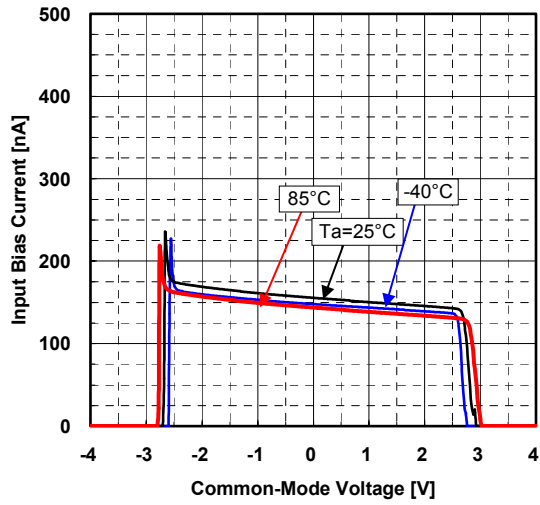




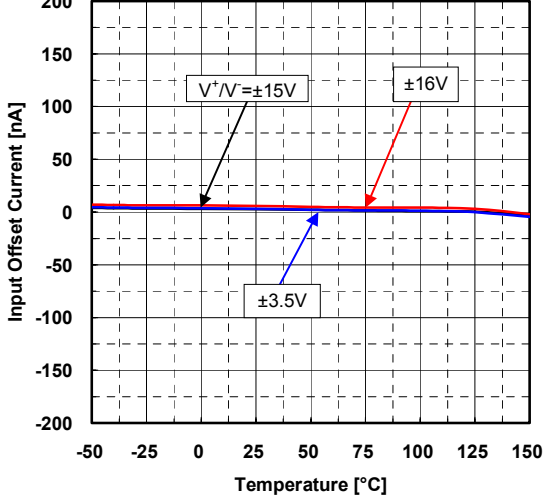
Input Bias Current vs. Input Common-Mode Voltage (Temperature)
 $V^+/V^- = \pm 15V$



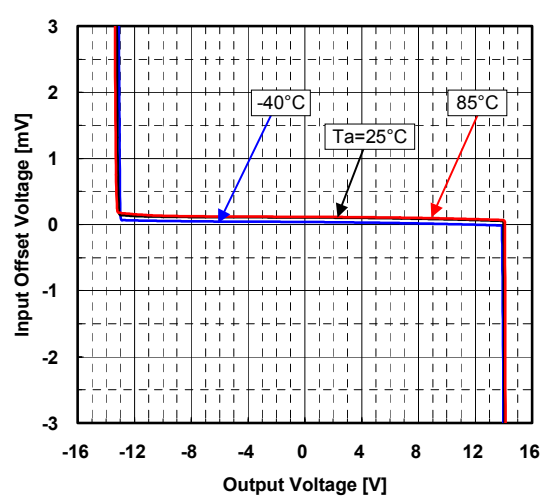
Input Bias Current vs. Input Common-Mode Voltage (Temperature)
 $V^+/V^- = \pm 3.5V$



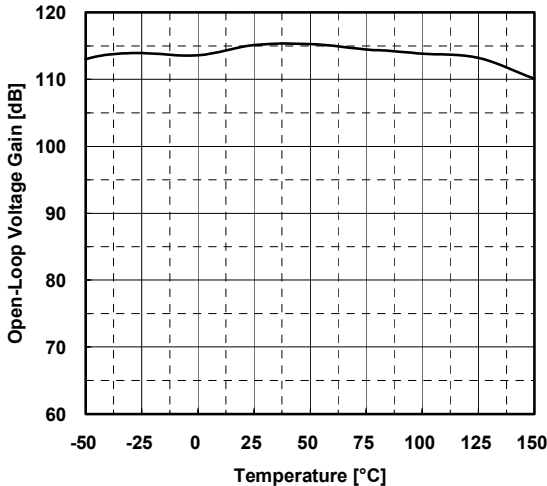
Input Offset Current vs. Temperature (Supply Voltage)
 $V_{icm} = 0V$



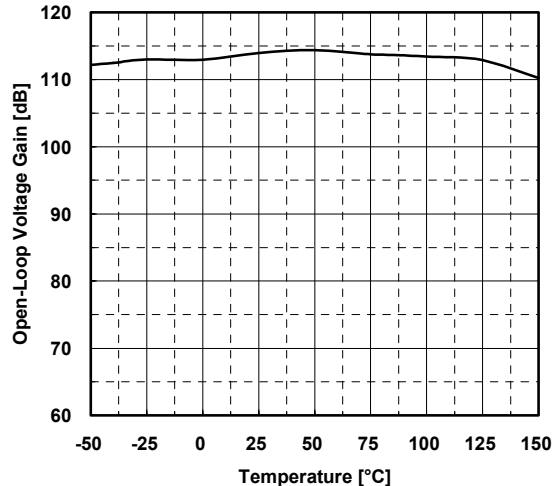
Input Offset Voltage vs. Output Voltage (Temperature)
 $V^+/V^- = \pm 15V, R_L = 2k\Omega$ to $0V$



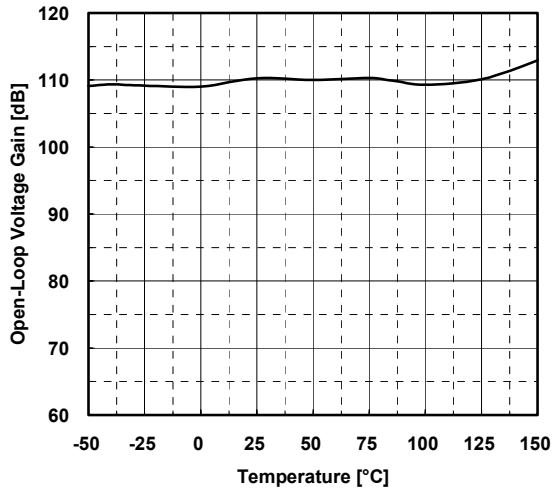
Open-Loop Voltage Gain vs. Temperature
 $R_L = 2k\Omega$ to $0V, V^+/V^- = \pm 16V, V_o = -11V$ to $+11V$



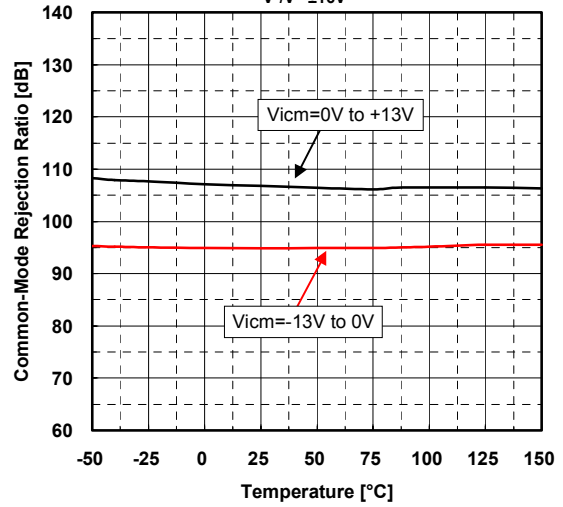
Open-Loop Voltage Gain vs. Temperature
 $R_L = 2k\Omega$ to $0V, V^+/V^- = \pm 15V, V_o = -10V$ to $+10V$



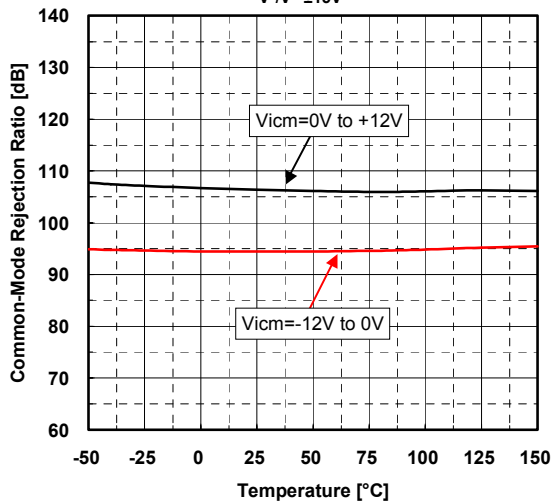
Open-Loop Voltage Gain vs. Temperature
 $R_L=2k\Omega$ to 0V, $V^+/V^-=\pm 3.5V$, $V_O=-1V$ to +1V



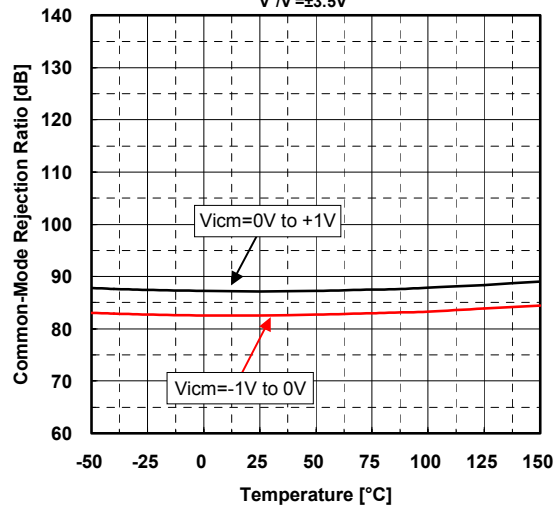
Common-Mode Rejection Ratio vs. Temperature (Input Common-Mode Voltage)
 $V^+/V^-=\pm 16V$



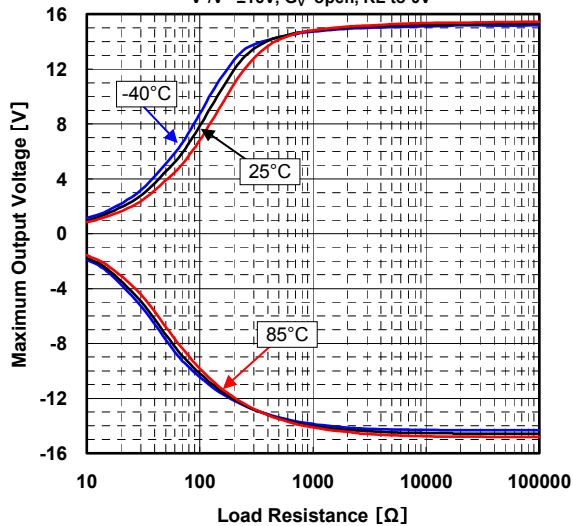
Common-Mode Rejection Ratio vs. Temperature (Input Common-Mode Voltage)
 $V^+/V^-=\pm 15V$



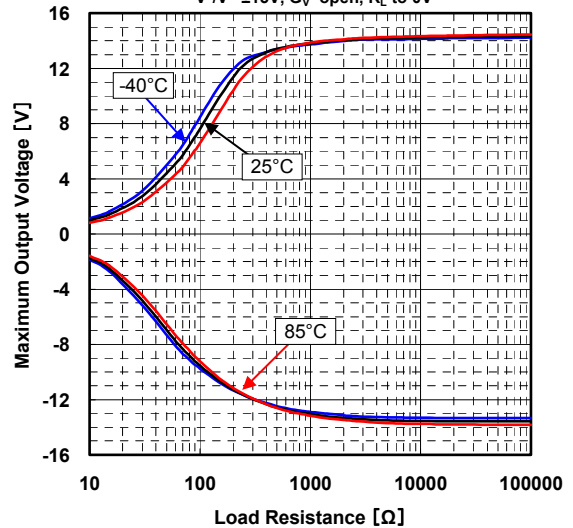
Common-Mode Rejection Ratio vs. Temperature (Input Common-Mode Voltage)
 $V^+/V^-=\pm 3.5V$

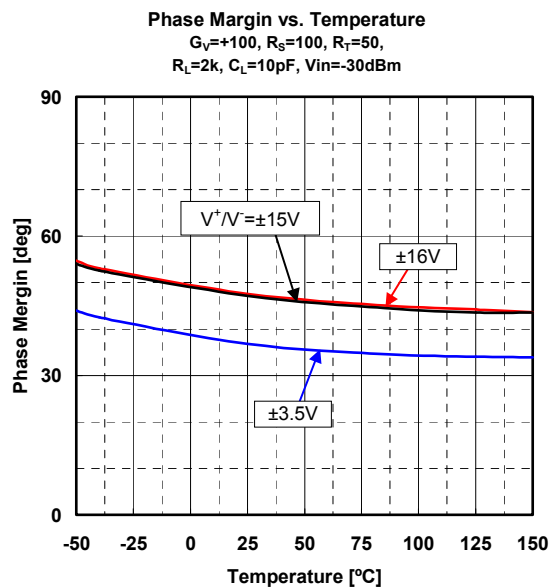
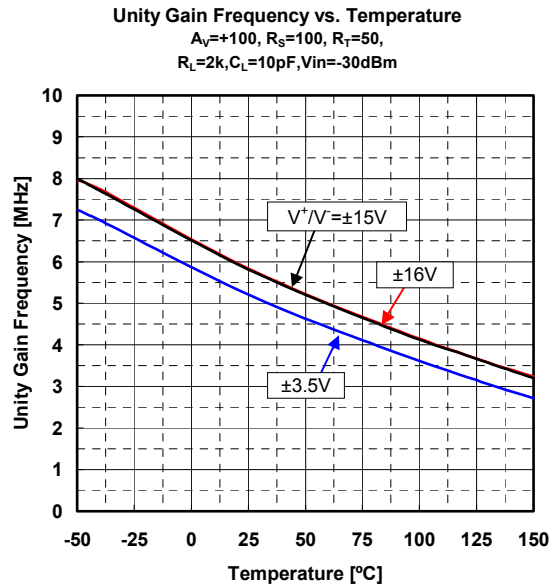
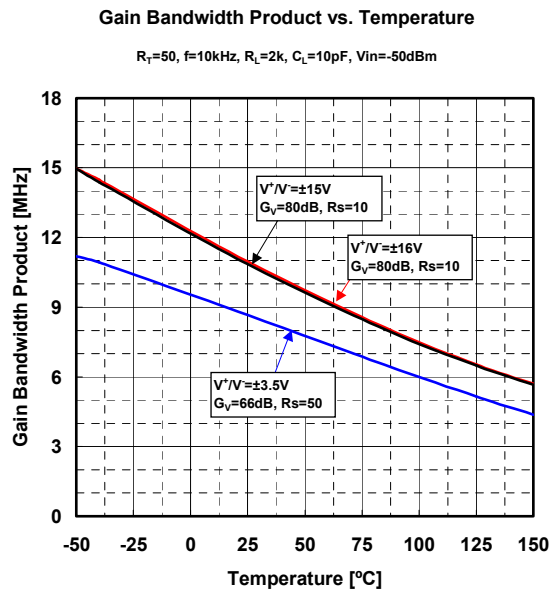
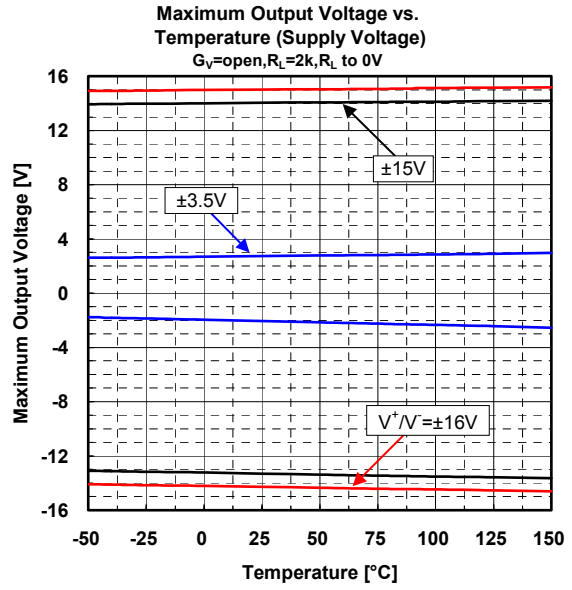
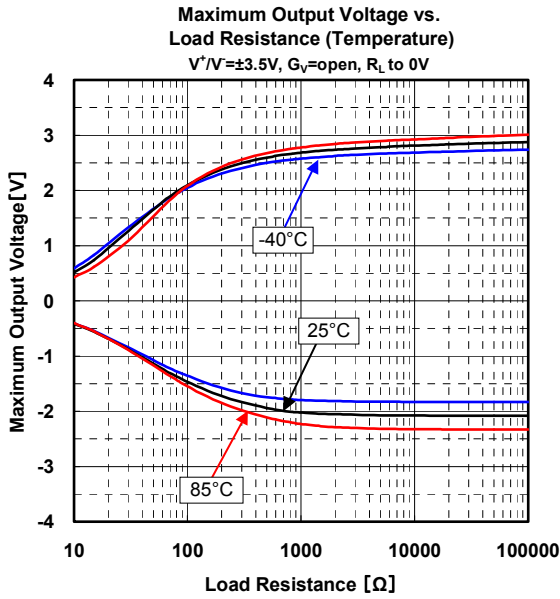


Maximum Output Voltage vs. Load Resistance (Temperature)
 $V^+/V^-=\pm 16V$, $G_V=open$, R_L to 0V



Maximum Output Voltage vs. Load Resistance (Temperature)
 $V^+/V^-=\pm 15V$, $G_V=open$, R_L to 0V





MUSES8820

MEMO

[CAUTION]
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- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
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- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.